## **Analogue Electronics 1 (EE204FZ)**

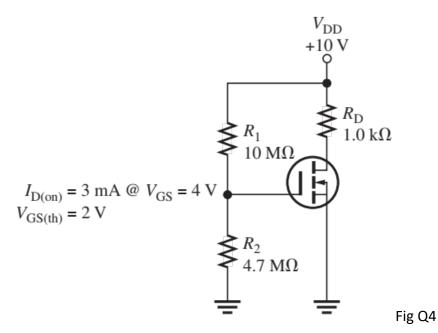
## Tutorial 1

Q1. Circle the correct answer.	
<ol> <li>In applications where</li> <li>bipolar transistor.</li> <li>Low</li> <li>Very low</li> <li>Zero</li> <li>High</li> </ol>	input resistance is needed, the JFET is preferred to the
2. A JFET always operates with A. the drain connected to ground B. the gate-to-source p-n junction forw C. the gate-to-source p-n junction reve D. the gate connected to the source	vard-biased
<ul> <li>3. An n-channel depletion-type MOSFE</li> <li>A. the depletion mode</li> <li>B. the enhancement mode</li> <li>C. the cutoff region</li> <li>D. saturation</li> </ul>	T with a positive $V_{GS}$ is operating in
<ul><li>4. All MOSFETs are subject to damage</li><li>A. excessive heat</li><li>B. electrostatic discharge</li><li>C. excessive voltage</li><li>D. All of the above</li></ul>	from
<ul> <li>5. In an enhancement-type MOSFET, the contract of the</li></ul>	nere is no drain current until $V_{ extsf{GS}}$
<ul><li>Q2. Answer the following questions.</li><li>1. Describe the two types of MOSFETs</li></ul>	and explain briefly how they function.
2. Describe the three regions of operat	tion of an enhancement-type MOSFET.

Q4. Find  $V_{GS}$  and  $V_{DS}$  for the enhancement-type MOSFET in Figure Q4. Datasheet information is listed with the circuit.

Q3. Sketch the transfer curve ( $I_D$  vs.  $V_{GS}$  in the saturation region) of a p-channel JFET with  $I_{DSS} = 4$ 

mA and  $V_P = 3$  V. Label  $I_{DSS}$  and  $V_P$  in the graph.



Q5. Based on the  $V_{GS}$  measurements, determine the drain current and drain-to-source voltage for the circuit in Figure Q5.

